



## General Purpose Transistors 三极管

### PNP Silicon (FHT1037)

#### FEATURES 特点

- Excellent  $h_{FE}$  Linearity  $h_{FE}$  线性特性极好  
:  $h_{FE}(0.1mA)/h_{FE}(2mA)=0.95(Typ.)$
- Low Noise 低噪声:  $NF=1dB(Typ.), 10dB(Max.)$ .
- Complementary to FHT2412 与 FHT2412 互补

#### MAXIMUM RATINGS( $T_a=25$ ) 最大额定值

| CHARACTERISTIC 特性参数                   | Symbol 符号 | Rating 额定值 | Unit 单位 |
|---------------------------------------|-----------|------------|---------|
| Collector-Base Voltage 集电极-基极电压       | $V_{CBO}$ | -60        | Vdc     |
| Collector-Emitter Voltage 集电极-发射极电压   | $V_{CEO}$ | -50        | Vdc     |
| Emitter-Base Voltage 发射极-基极电压         | $V_{EBO}$ | -6.0       | Vdc     |
| Collector Current—Continuous 集电极电流-连续 | $I_C$     | -150       | mAdc    |
| Base Current 基极电流                     | $I_B$     | -30        | mAdc    |
| Collector Power Dissipation 集电极耗散功率   | $P_C$     | 200        | mW      |
| Junction Temperature 结温               | $T_j$     | 150        |         |
| Storage Temperature Range 储存温度        | $T_{stg}$ | -55 ~ 150  |         |

#### DEVICE MARKING 打标

$h_{FE}(1)FHT1037Q=FQ(120 \sim 270), FHT1037R=FR(180 \sim 390), FHT1037S=FS(270 \sim 560)$

#### ELECTRICAL CHARACTERISTICS 电特性

( $T_A=25$  unless otherwise noted 如无特殊说明, 温度为 25 )

| Characteristic 特性参数                              | Symbol 符号     | Test Condition 测试条件             | Min 最小值 | TYP 典型 | Max 最大值 | Unit 单位 |
|--|---------------|---------------------------------|---------|--------|---------|---------|
| Collector Cutoff Current 集电极截止电流                 | $I_{CBO}$     | $V_{CB}=-60V, I_E=0$            | —       | —      | -0.1    | $\mu A$ |
| Emitter Cutoff Current 发射极截止电流                   | $I_{EBO}$     | $V_{EB}=-6V, I_C=0$             | —       | —      | -0.1    | $\mu A$ |
| Collector-Base Breakdown Voltage 集电极-基极击穿电压      | $V_{(BR)CBO}$ | $I_C=-50\mu A$                  | -60     | —      | —       | V       |
| Collector-Emitter Breakdown Voltage 集电极-发射极击穿电压  | $V_{(BR)CEO}$ | $I_C=-1.0mA$                    | -50     | —      | —       | V       |
| Emitter-Base Breakdown Voltage 发射极-基极击穿电压        | $V_{(BR)EBO}$ | $I_E=-50\mu A$                  | -6      | —      | —       | V       |
| DC Current Gain 直流电流增益                           | $h_{FE}$      | $V_{CE}=-6V, I_C=-1mA$          | 120     | —      | 560     | —       |
| Collector-Emitter Saturation Voltage 集电极-发射极饱和压降 | $V_{CE(sat)}$ | $I_C=-50mA, I_B=-5mA$           | —       | —      | -0.5    | V       |
| Transition Frequency 特征频率                        | $f_T$         | $V_{CE}=-12V, I_E=2mA, f=30MHz$ | —       | 140    | —       | MHz     |
| Collector Output Capacitance 输出电容                | $C_{ob}$      | $V_{CB}=-12V, I_E=0, f=1MHz$    | —       | 4.0    | 5.0     | pF      |



## SOT-23 封装外形尺寸 (SOT-23 DIMENSION)

